



SUD50N03-12P-GE3 Information



For Reference Only

Part Number SUD50N03-12P-GE3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 16.8A TO252 **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SUD50N03-12P-GE3 Specifications

Manufacturer Part Number SUD50N03-12P-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 16.8A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 42nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1600pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 39W (Tc) Rds On (Max) @ Id, Vgs 17 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C16.8A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs42nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)39W (Tc)Rds On (Max) @ Id, Vgs17 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	TrenchFET?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 20A, 10V Operating Temperature Supplier Device Package Package / Case 16.8A (Ta) 16.8A	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs42nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)39W (Tc)Rds On (Max) @ Id, Vgs17 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	16.8A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)39W (Tc)Rds On (Max) @ Id, Vgs17 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	42nC @ 10V
FET Feature - 39W (Tc) Rds On (Max) @ Id, Vgs 17 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	1600pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs17 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	39W (Tc)
Mounting Type Surface Mount Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	17 mOhm @ 20A, 10V
Supplier Device Package TO-252 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	TO-252
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

SUD50N03-12P-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SUD50N03-12P-GE3 Payment Methods



















SUD50N03-12P-GE3 Shipping Methods













If you have any question about SUD50N03-12P-GE3, please do not hesitate to contact us!

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